TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# TC74AC74P,TC74AC74F,TC74AC74FN,TC74AC74FT

#### Dual D-Type Flip Flop with Preset and Clear

The TC74AC74 is an advanced high speed CMOS D-FLIP FLOP fabricated with silicon gate and double-layer metal wiring C<sup>2</sup>MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

The signal level applied to the D INPUT is transferred to Q OUTPUT during the positive going transition of the CK pulse.

 $\overline{\text{CLR}}$  and  $\overline{\text{PR}}$  are independent of the CK and are accomplished by setting the appropriate input to an "L" level.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

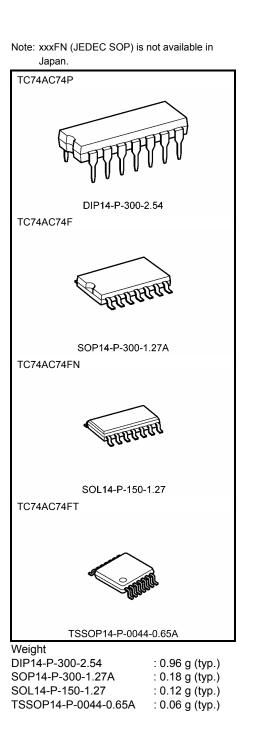
#### Features

- High speed:  $f_{max} = 200 \text{ MHz}$  (typ.) at  $V_{CC} = 5 \text{ V}$
- Low power dissipation:  $I_{CC} = 4 \mu A (max)$  at  $Ta = 25^{\circ}C$
- High noise immunity: V<sub>NIH</sub> = V<sub>NIL</sub> = 28% V<sub>CC</sub> (min)
- Symmetrical output impedance: |IOH| = IOL = 24 mA (min)

Capability of driving 50  $\Omega$ 

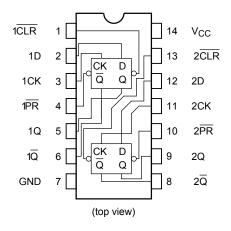
transmission lines.

- Balanced propagation delays:  $t_{pLH}\simeq t_{pHL}$
- Wide operating voltage range: V<sub>CC</sub> (opr) = 2 V to 5.5 V
- Pin and function compatible with 74F74

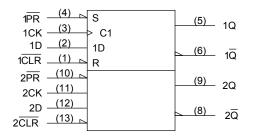


# <u>TOSHIBA</u>

# **Pin Assignment**



# **IEC Logic Symbol**

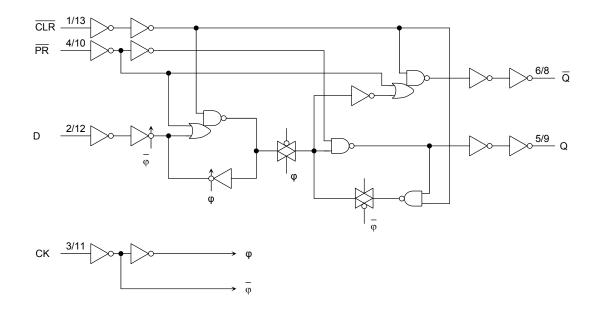


### **Truth Table**

	Inp	uts		Out	puts	Function	
CLR	PR	D	СК	Q	Q	T UNCLOIT	
L	Н	Х	Х	L	Н	Clear	
Н	L	Х	х	Н	L	Preset	
L	L	Х	Х	Н	Н	_	
Н	Н	L		L	Н	_	
Н	Н	Н		Н	L	_	
Н	Н	Х		Qn	$\overline{Q}_{n}$	No Change	

X: Don't care

# System Diagram



### Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5 to 7.0	V
DC input voltage	V <sub>IN</sub>	-0.5 to V <sub>CC</sub> + 0.5	V
DC output voltage	V <sub>OUT</sub>	-0.5 to V <sub>CC</sub> + 0.5	V
Input diode current	I <sub>IK</sub>	±20	mA
Output diode current	I <sub>OK</sub>	±50	mA
DC output current	IOUT	±50	mA
DC V <sub>CC</sub> /ground current	ICC	±100	mA
Power dissipation	PD	500 (DIP) (Note 2)/180 (SOP/TSSOP)	mW
Storage temperature	T <sub>stg</sub>	−65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 2: 500 mW in the range of Ta = −40°C to 65°C. From Ta = 65°C to 85°C a derating factor of −10 mW/°C should be applied up to 300 mW.

Characteristics	Symbol	Rating	Unit	
Supply voltage	V <sub>CC</sub>	2.0 to 5.5	V	
Input voltage	V <sub>IN</sub>	0 to V <sub>CC</sub>	V	
Output voltage	V <sub>OUT</sub>	0 to V <sub>CC</sub>	V	
Operating temperature	T <sub>opr</sub>	-40 to 85	°C	
Input rise and fall time	dt/dV	0 to 100 (V <sub>CC</sub> = 3.3 ± 0.3 V)	ns/V	
	u/uv	0 to 20 (V <sub>CC</sub> = 5 $\pm$ 0.5 V)	115/ V	

### **Operating Ranges (Note)**

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

## **Electrical Characteristics**

#### **DC Characteristics**

Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = −40 to 85°C		Unit		
Characteristics	Symbol				V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Onit	
					2.0	1.50	_	_	1.50	_		
High-level input voltage	VIH		_		3.0	2.10	—	—	2.10	—	V	
					5.5	3.85	-	-	3.85	—		
					2.0		-	0.50	-	0.50		
Low-level input voltage	VIL	—			3.0	_	_	0.90	—	0.90	V	
Ũ					5.5		_	1.65	-	1.65		
	Vон				2.0	1.9	2.0	—	1.9	—	v	
		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> = -50 μA	3.0	2.9	3.0	_	2.9	—			
High-level output					4.5	4.4	4.5	-	4.4	—		
voltage			I <sub>OH</sub> = -4 mA		3.0	2.58			2.48	—	V	
			I <sub>OH</sub> = −24 mA		4.5	3.94	_	_	3.80	—		
			I <sub>OH</sub> = −75 mA	(Note)	5.5		-	-	3.85	—		
	V <sub>OL</sub>	VIN = V <sub>IH</sub> or VIL			2.0	_	0.0	0.1	—	0.1		
			I <sub>OL</sub> = 50 μA		3.0	_	0.0	0.1	—	0.1		
Low-level output					4.5		0.0	0.1	-	0.1	v	
voltage			I <sub>OL</sub> = 12 mA		3.0	—	—	0.36	—	0.44	v	
			I <sub>OL</sub> = 24 mA		4.5	_	—	0.36	—	0.44		
			I <sub>OL</sub> = 75 mA	(Note)	5.5		-	-	-	1.65		
Input leakage current	I <sub>IN</sub>	V <sub>IN</sub> = V <sub>CC</sub> or GND		5.5	_	_	±0.1		±1.0	μA		
Quiescent supply current	Icc	V <sub>IN</sub> = V <sub>CC</sub> or GND			5.5	_	_	4.0	-	40.0	μA	

Note: This spec indicates the capability of driving 50  $\Omega$  transmission lines.

One output should be tested at a time for a 10 ms maximum duration.

#### Timing Requirements (input: tr = tf = 3 ns)

Characteristics	Symbol	Test Condition	Ta = 25°C	Ta = -40 to 85°C	Unit	
			V <sub>CC</sub> (V)	Limit	Limit	
Minimum pulse width	t <sub>w (L)</sub>		3.3 ± 0.3	7.0	7.0	
(CK)	t <sub>w (H)</sub>	—	$5.0 \pm 0.5$	5.0	5.0	ns
Minimum pulse width			3.3 ± 0.3	7.0	7.0	
( CLR , PR )	t <sub>w (L)</sub>	—	5.0 ± 0.5	5.0	5.0	ns
	ts	—	3.3 ± 0.3	6.0	6.0	ns
Minimum set-up time			5.0 ± 0.5	3.5	3.5	
Minimum hald time			3.3 ± 0.3	1.0	1.0	
Minimum hold time	t <sub>h</sub>	—	$5.0 \pm 0.5$	1.0	1.0	ns
Minimum removal time			3.3 ± 0.3	4.0	4.0	
$(\overline{CLR}, \overline{PR})$	t <sub>rem</sub>	—	5.0 ± 0.5	2.0	2.0	ns

#### AC Characteristics (C<sub>L</sub> = 50 pF, R<sub>L</sub> = 500 $\Omega$ , input: t<sub>r</sub> = t<sub>f</sub> = 3 ns)

Characteristics	Symbol	Test Condition		Ta = 25°C			Ta = −40 to 85°C		Unit
	,		V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	
Propagation delay time $(CK-Q, \overline{Q})$	t <sub>pLH</sub> t <sub>pHL</sub>	_	3.3 ± 0.3 5.0 ± 0.5		8.2 6.1	13.9 8.7	1.0 1.0	16.0 10.0	ns
Propagation delay time $(\overline{\text{CLR}}, \overline{\text{PR}} - \text{Q}, \overline{\text{Q}})$	t <sub>pLH</sub> t <sub>pHL</sub>	_	3.3 ± 0.3 5.0 ± 0.5		8.0 5.7	13.1 8.2	1.0 1.0	15.0 9.4	ns
Maximum clock frequency	f <sub>max</sub>	_	3.3 ± 0.3 5.0 ± 0.5	60 100	120 160	_	60 100	_	MHz
Input capacitance	C <sub>IN</sub>	—		_	5	10	_	10	pF
Power dissipation capacitance	C <sub>PD</sub>		(Note)	_	77	—	_	_	pF

Note: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

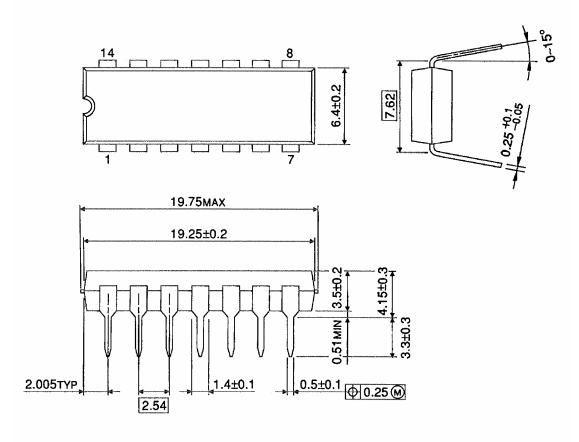
Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2 (per F/F)$ 

## **Package Dimensions**

DIP14-P-300-2.54

Unit : mm



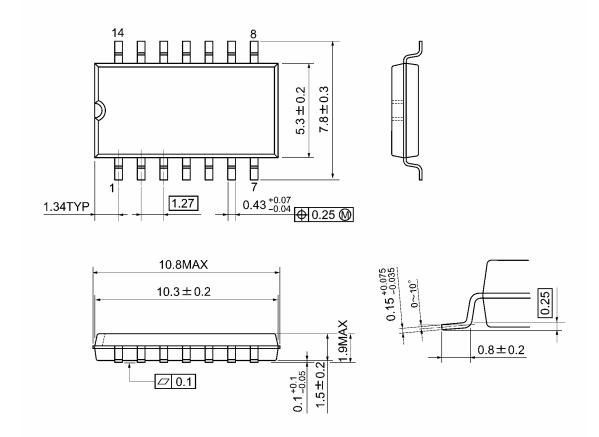
Weight: 0.96 g (typ.)

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## **Package Dimensions**

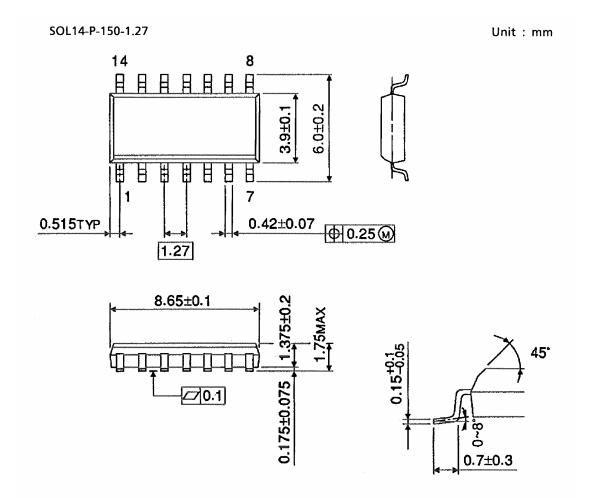
SOP14-P-300-1.27A

Unit: mm



Weight: 0.18 g (typ.)

## Package Dimensions (Note)



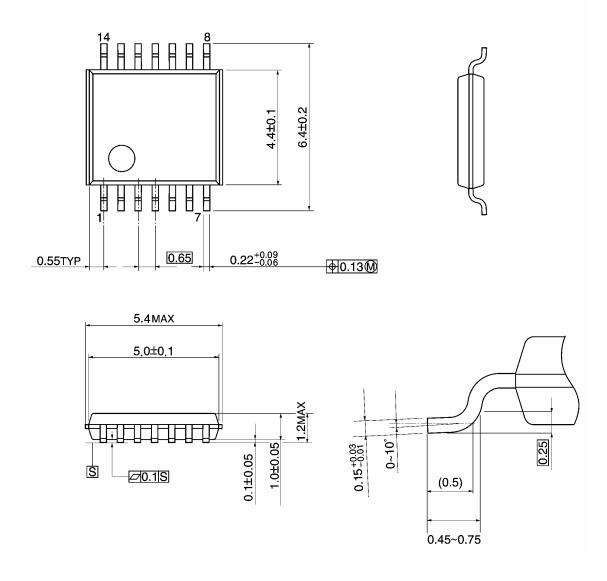
Note: This package is not available in Japan.

Weight: 0.12 g (typ.)

## **Package Dimensions**

TSSOP14-P-0044-0.65A

Unit: mm



Weight: 0.06 g (typ.)

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20070701-EN GENERAL

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